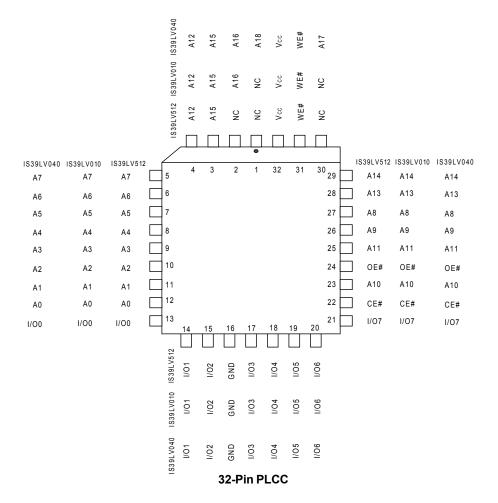
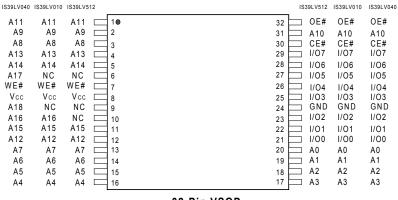


CONNECTION DIAGRAMS





32-Pin VSOP

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PIN DESCRIPTIONS

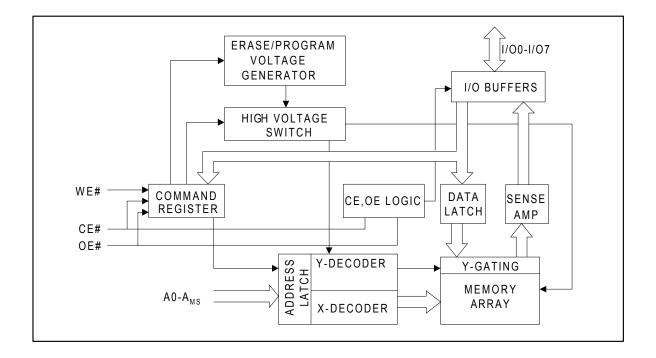
SYMBOL	TYPE	DESCRIPTION
A0 - A _{MS} ⁽¹⁾	INPUT	Address Inputs: For memory addresses input. Addresses are internally latched on the falling edge of WE# during a write cycle.
CE#	INPUT	Chip Enable: CE# goes low activates the device's internal circuitries for device operation. CE# goes high deselects the device and switches into standby mode to reduce the power consumption.
WE#	INPUT	Write Enable: Activate the device for write operation. WE# is active low.
OE#	INPUT	Output Enable: Control the device's output buffers during a read cycle. OE# is active low.
1/00 - 1/07	INPUT/ OUTPUT	Data Inputs/Outputs: Input command/data during a write cycle or output data during a read cycle. The I/O pins float to tri-state when OE# are disabled.
VCC		Device Power Supply
GND		Ground
NC		No Connection

Note:

1. A_{MS} is the most significant address where A_{MS} = A15 for IS39LV512, A16 for IS39LV010, and A18 for IS39LV040.



BLOCK DIAGRAM



DEVICE OPERATION READ OPERATION

The access of IS39LV512/010/040 are similar to EPROM. To read data, three control functions must be satisfied:

 \bullet CE# is the chip enable and should be pulled low (V_{IL}).

- OE# is the output enable and should be pulled low (V_{IL}).

+ WE# is the write enable and should remains high (V_{IH}).

PRODUCT IDENTIFICATION

The product identification mode can be used to identify the manufacturer and the device through hardware or software read ID operation. See Table 1 for pFLASH[™] Manufacturer ID and Device ID. The hardware ID mode is activated by applying a 12.0 Volt on A9 pin, typically used by an external programmer for selecting the right programming algorithm for the devices. Refer to Table 2 for Bus Operation Modes. The software ID mode is activated by a three-bus-cycle command. See Table 3 for Software Command Definition.

BYTE PROGRAMMING

The programming is a four-bus-cycle operation and the data is programmed into the devices (to a logical "0") on a byte-by-byte basis. See Table 3 for Software Command Definition. A program operation is activated by writing the three-byte command sequence followed by program address and one byte of program data into the devices. The addresses are latched on the falling edge of WE# or CE# whichever occurs later, and the data are latched on the rising edge of WE# or CE# whichever occurs first. The internal control logic automatically handles the internal programming voltages and timing.

A data "0" can not be programmed back to a "1". Only erase operation can convert the "0"s to "1"s. The Data# Polling on I/O7 or Toggle Bit on I/O6 can be used to detect the progress or completion of a program cycle.



DEVICE OPERATION (CONTINUED)

CHIP ERASE

The entire memory array can be erased through a chip erase operation. Pre-programs the devices are not required prior to a chip erase operation. Chip erase starts immediately after a six-bus-cycle chip erase command sequence. All commands will be ignored once the chip erase operation has started. The devices will return to standby mode after the completion of chip erase.

SECTOR AND BLOCK ERASE

The memory array of IS39LV512/010/040 are organized into uniform 4 Kbyte sectors. A sector erase operation allows to erase any individual sector without affecting the data in others. The memory array of IS39LV010/040, excluding IS39LV512, are also organized into uniform 64 Kbyte blocks (sector group - consists of sixteen adjacent sectors). A block erase operation allows to erase any individual block. The sector or block erase operation is similar to chip erase.

I/O7 DATA# POLLING

The IS39LV512/010/040 provide a Data# Polling feature to indicate the progress or completion of a program and erase cycles. During a program cycle, an attempt to read the devices will result in the complement of the last loaded data on I/O7. Once the program operation is completed, the true data of the last loaded data is valid on all outputs. During a sector, block, or chip erase cycle, an attempt to read the device will result a "0" on I/O7. After the erase operation is completed, an attempt to read the device will result a "1" on I/O7.

I/O6 TOGGLE BIT

The IS39LV512/010/040 also provide a Toggle Bit feature to detect the progress or completion of a program and erase cycles. During a program or erase cycle, an attempt to read data from the device will result a toggling between "1" and "0" on I/O6. When the program or erase operation is complete, I/O6 will stop toggling and valid data will be read. Toggle bit may be accessed at any time during a program or erase cycle.

HARDWARE DATA PROTECTION

Hardware data protection protects the devices from unintentional erase or program operation. It is performed in the following ways: (a) V_{CC} sense: if V_{CC} is below 1.8 V (typical), the write operation is inhibited. (b) Write inhibit: holding any of the signal OE# low, CE# high, or WE# high inhibits a write cycle. (c) Noise filter: pulses of less than 5 ns (typical) on the WE# or CE# input will not initiate a write operation.

Table 1. Product Identification

Product Identification	Data
Manufacturer ID	9Dh
Device ID:	
IS39LV512	1Bh
IS39LV010	1Ch
IS39LV040	3Eh



SECTOR/BLOCK ADDRESS TABLE

Memory Density		Block	Block Size (Kbytes)	Sector	Sector Size (Kbytes)	Address Range				
					Sec- tor 0	4	00000h - 00FFFh			
512Kbit			Block 0 ⁽²⁾	64	Sec- tor 1	4	01000h - 01FFFh			
					:	:	:			
	1 Mbit				Sector 15	4	0F000h - 0FFFFh			
		4 Mbit					Sector 16	4	10000h - 10FFFh	
			Block 1	64	Sector 17	4	11000h - 11FFFh			
			4 Mbit	4 Mbit	4 Mbit	Mbit		:	:	:
							Sector 31	4	1F000h - 1FFFFh	
			Block 2	64	در	œ	20000h - 2FFFFh			
			Block 3	64	α	α	30000h - 3FFFFh			
			Block 4	64	α	ű	40000h - 4FFFFh			
			Block 5	64	α	«	50000h - 5FFFFh			
			Block 6	64	ű	ű	60000h - 6FFFFh			
			Block 7	64	α	"	70000h - 7FFFFh			

Notes:

- 1. A Block is a 64 Kbyte sector group which consists of sixteen adjecent sectors of 4 Kbyte each.
- 2. Block erase feature is available for IS39LV010/040 only. The chip erase command should be used to erase the Block 0 for the IS39LV512.



OPERATING MODES

Mode	CE#	OE#	WE#	ADDRESS	I/O
Read	V _{IL}	V _{IL}	V _{IH}	X (1)	D _{OUT}
Write	V _{IL}	V _{IH}	V _{IL}	X	D _{IN}
Standby	V _{IH}	х	х	×	High Z
Output Disable	х	V _{IH}	х	×	High Z
Product Identifi-	N	V	V	A2 - $A_{MS}^{(2)}$ = X, A9 = $V_{H}^{(3)}$, A1 = V_{IL} , A0 = V_{IL}	Manufacturer ID
cation Hardware	V _{IL}	V _{IL} V _{IH}	VIH	$A2 - A_{MS}^{(2)} = X, A9 = V_{H}^{(3)}, A1 = V_{IL}, A0 = V_{IH}$	Device I

Table 2. Bus Operation Modes

Notes:

- 1. X can be V_{IL} , V_{IH} or addresses.
- 2. A_{MS} = Most significant address; A_{MS} = A15 for IS39LV512, A16 for IS39LV010, and A18 for IS39LV040.

 $3.V_{H} = 12.0 V \pm 0.5 V.$



COMMAND DEFINITION

Command Sequence	Bus Cycle	1st Bus Cycle Addr Data	2nd Bus Cycle Addr Data	3rd Bus Cycle Addr Data	4th Bus Cycle Addr Data	5th Bus Cylce Addr Data	6th Bus Cycle Addr Data
Read	1	Addr D _{OUT}					
Chip Erase	6	555h AAh	2AAh 55h	555h 80h	555h AAh	2AAh 55h	555h 10h
Sector Erase	6	555h AAh	2AAh 55h	555h 80h	555h AAh	2AAh 55h	SA ⁽¹⁾ 30h
Block Erase	6	555h AAh	2AAh 55h	555h 80h	555h AAh	2AAh 55h	BA ⁽²⁾ 50h
Byte Program	4	555h AAh	2AAh 55h	555h A0h	Addr D _{IN}		
Product ID Entry	3	555h AAh	2AAh 55h	555h 90h			
Product ID Exit ⁽³⁾	3	555h AAh	2AAh 55h	555h F0h			
Product ID Exit ⁽³⁾	1	XXXh F0h					

Table 3. Software Command Definition

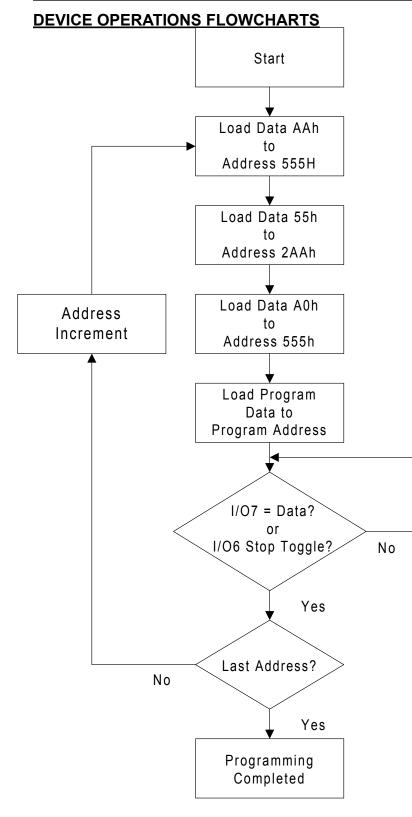
Notes:

1. SA = Sector address of the sector to be erased.

2. BA = Block address of the block to be erased.

3. Either one of the Product ID Exit command can be used.

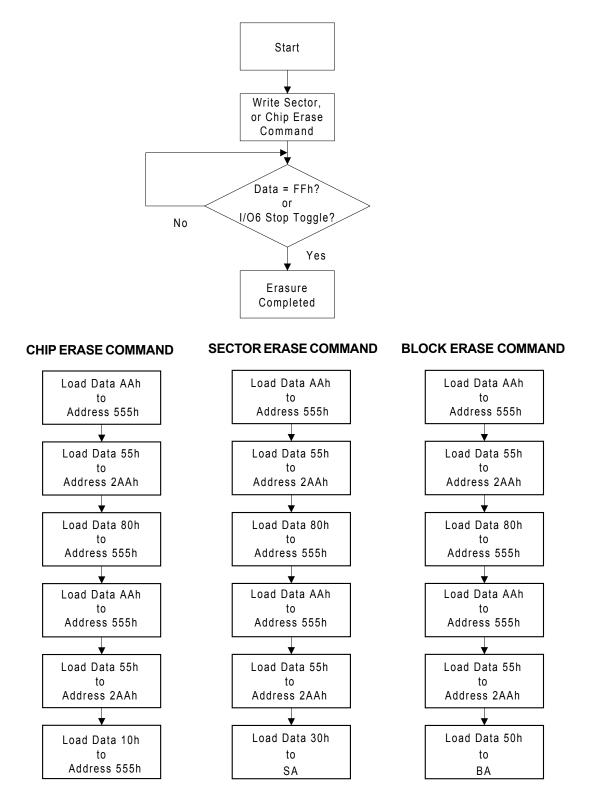








DEVICE OPERATIONS FLOWCHARTS (CONTINUED)

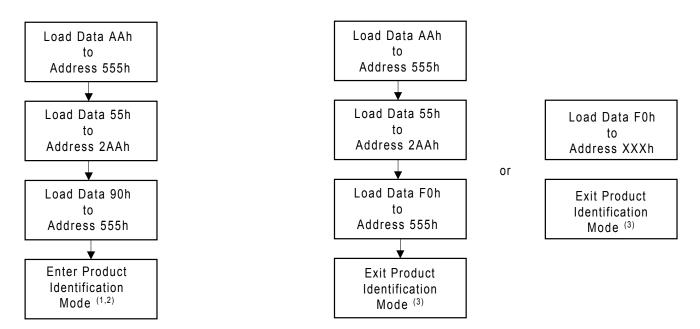




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DEVICE OPERATIONS FLOWCHARTS (CONTINUED)



Notes:

- 1. The device will enter Product Identification mode after excuting the Product ID Entry command.
- 2. Under Product Identification mode, the Manufacturer ID and Device ID of devices can be read at address X0000h and X0001h where X = Don't Care.
- 3. The device returns to standby operation.

Chart 3. Software Product Identification Entry/Exit Flowchart



ABSOLUTE MAXIMUM RATINGS (1)

Temperature Under Bias	-65°C to +125°C
	-65°C to +125°C
Storage Temperature	
Surface Mount Lead Soldering Temperature	240°C 3 Seconds
Input Voltage with Respect to Ground on All Pins except A9 pin (2)	-0.5V to VCC + 0.5 V
Input Voltage with Respect to Ground on A9 pin (3)	-0.5V to +13.0 V
All Output Voltage with Respect to Ground	-0.5V to VCC + 0.5 V
VCC (2)	-0.5V to +6.0 V

Notes:

- 1. Stresses under those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only. The functional operation of the device or any other conditions under those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating condition for extended periods may affected device reliability.
- 2. Maximum DC voltage on input or I/O pins are V_{CC} + 0.5V. During voltage transitioning period, input or I/O pins may overshoot to V_{CC} + 2.0V for a period of time up to 20 ns. Minimum DC voltage on input or I/O pins are -0.5V. During voltage transitioning period, input or I/O pins may undershoot GND to -2.0V for a period of time up to 20 ns.
- Maximum DC voltage on A9 pin is +13.0 V. During voltage transitioning period, A9 pin may overshoot to +14.0 V for a period of time up to 20 ns. Minimum DC voltage on A9 pin is -0.5V. During voltage transitioning period, A9 pin may undershoot GND to -2.0V for a period of time up to 20 ns.

DC AND AC OPERATING RANGE

Part Number	IS39LV512/010	IS39LV040
Operating Temperature	-40° to +85°C	0° to +85°C
Vcc Power Supply	2.70 V - 3.60 V	2.70 V - 3.60 V



DC CHARACTERISTICS

Symbol	Parameter	Condition	Min	Тур	Max	Units
ILI	Input Load Current	VIN= 0 V to V CC			1	mA
ILO	Output Leakage Current	VI/O = 0 V to V CC			1	mA
ISB1	VCC Standby Current CMOS	CE#, OE# = V CC -0.3 V		0.1	5	mA
ISB2	VCC Standby Current TTL	CE# = VIH to VCC		0.05	3	mA
ICC1	VCC Active Read Current	f = 5 MHz; IOUT = 0 mA		4	15	mA
ICC2(1)	VCC Program/Erase Cur- rent			8	20	mA
VIL	Input Low Voltage		-0.5		0.8	V
VIH	Input High Voltage		0.7 VCC		VCC + 0.3	V
VOL	Output Low Voltage	IOL = 2.1 mA; VCC = VCCmin			0.45	V
VOH	Output High Voltage	IOH = -100 mA; VCC = VCC min	VCC - 0.2			V

Note: 1. Characterized but not 100% tested.



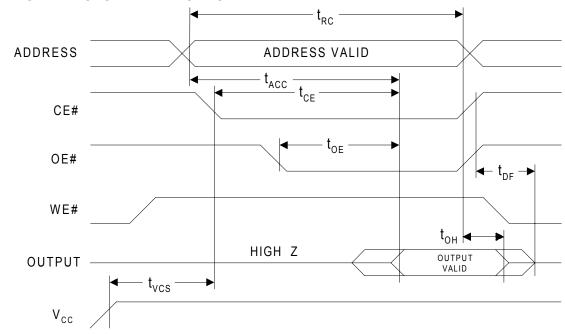
AC CHARACTERISTICS

READ OPERATIONS CHARACTERISTICS

Symbol	Parameter	IS39LV512/010	/040	Units
tRC	Read Cycle Time	70		ns
tACC	Address to Output Delay		70	ns
tCE	CE# to Output Delay		70	ns
tOE	OE# to Output Delay		35	ns
tDF	CE# or OE# to Output High Z	0	25	ns
tOH	Output Hold from OE#, CE# or Address, which- ever occured first	0		ns
tVCS	VCC Set-up Time	50		ms

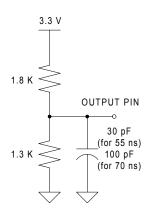


AC CHARACTERISTICS (CONTINUED)



READ OPERATIONS AC WAVEFORMS

OUTPUT TEST LOAD



INPUT TEST WAVEFORMS AND MEASUREMENT LEVEL



PIN CAPACITANCE ($f = 1 \text{ MHz}, T = 25^{\circ}\text{C}$)

	Тур	Max	Units	Conditions
C _{IN}	4	6	pF	V _{IN} = 0 V
C _{OUT}	8	12	pF	V _{OUT} = 0 V

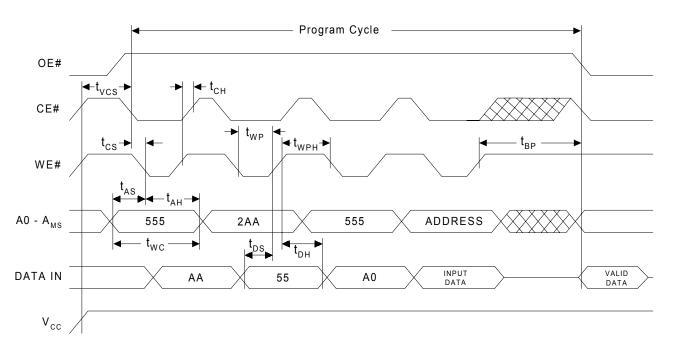
Note: These parameters are characterized but not 100% tested.



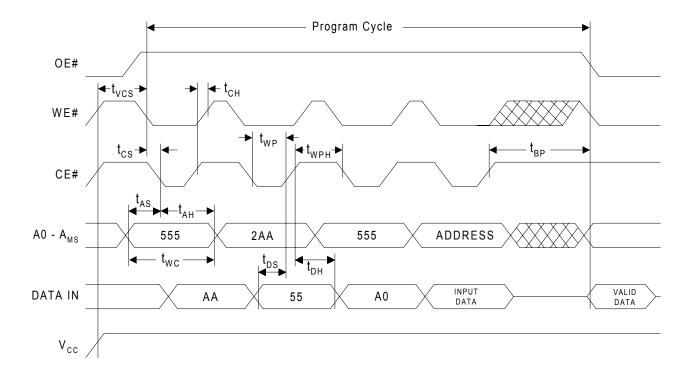
WRITE (PROGRAM/ERASE) OPERATIONS CHARACTERISTICS

Cumhal	Devenuetor	IS39LV512/010/04	– Units	
Symbol	Parameter	Min	Max	Units
tWC	Write Cycle Time	70		ns
tAS	Address Set-up Time	0		ns
tAH	Address Hold Time	30		ns
tCS	CE# and WE# Set-up Time	0		ns
tCH	CE# and WE# Hold Time	0		ns
tOEH	OE# High Hold Time	10		ns
tDS	Data Set-up Time	40		ns
tDH	Data Hold Time	0		ns
tWP	Write Pulse Width	35		ns
tWPH	Write Pulse Width High	20		ns
tBP	Byte Programming Time		40	ms
tEC	Chip or Block Erase Time		100	ms
tVCS	VCC Set-up Time	50		ms

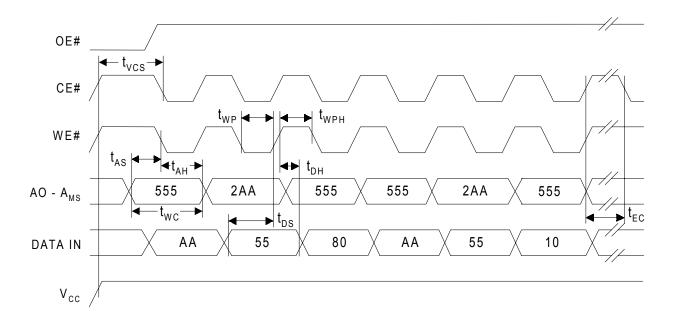
PROGRAM OPERATIONS AC WAVEFORMS - WE# CONTROLLED



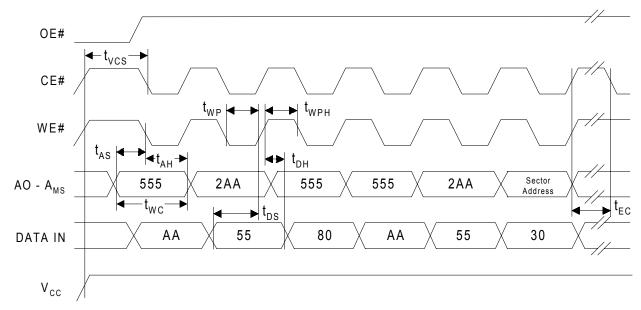




CHIP ERASE OPERATIONS AC WAVEFORMS

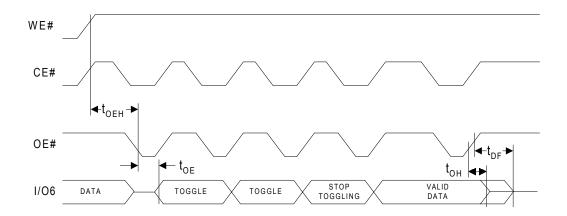






SECTOR OR BLOCK ERASE OPERATIONS AC WAVEFORMS

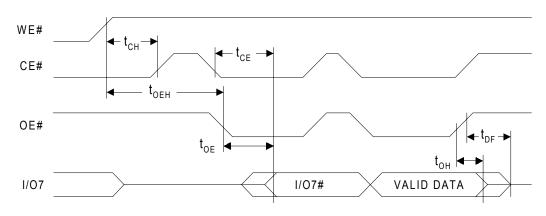
TOGGLE BIT AC WAVEFORMS



Note: Toggling CE#, OE#, or both OE# and CE# will operate Toggle Bit.



DATA# POLLING AC WAVEFORMS



Note: Toggling CE#, OE#, or both OE# and CE# will operate Data# Polling.

PROGRAM/ERASE PERFORMANCE

Parameter	Unit	Тур	Мах	Remarks
Sector Erase Time	ms	55	100	From writing erase command to erase completion
Block Erase Time	ms	55	100	From writing erase command to erase completion
Chip Erase Time	ms	55	100	From writing erase command to erase completion
Byte Programming Time	ms	16	20	Excludes the time of four-cycle program command execution

Note: 1. These parameters are characterized but not 100% tested.

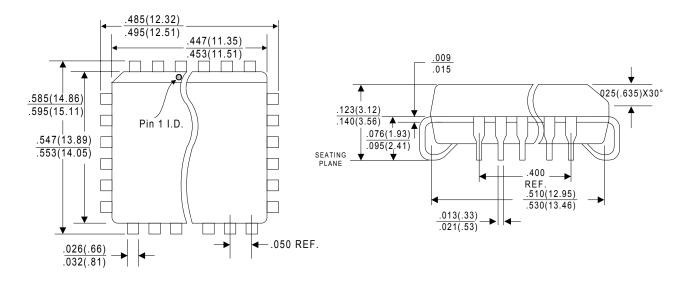
2. Preliminary specification only and will be formalized after cycling qualification test.



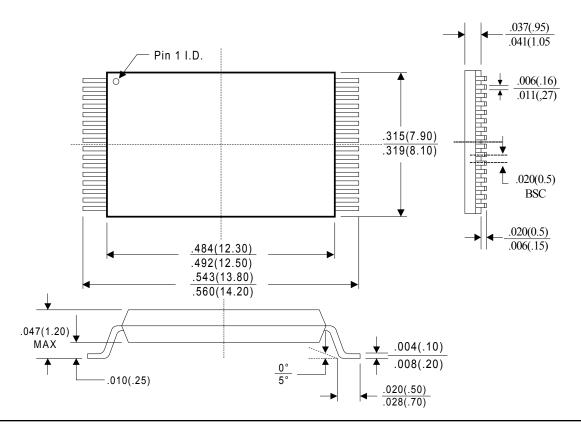
PACKAGE TYPE INFORMATION

PLCC

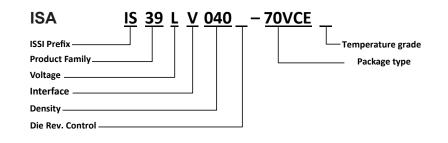
32-Pin Plastic Leaded Chip Carrier Dimensions in Inches (Millimeters)











Flash Product Family	ISA Interface	Package Type	Lead-Free Package
ISA = 29/39	V = ISA x8 L = ISA x8/x16	JE = 48 pin TSSOP JT = 56 pin TSSOP	E/L = Lead-Free
ISA Operating Voltage Range G/L = 2.70-3.60V Die Rev. Control	Density 025 = 256Kb 512 = 512Kb 010 = 1Mb	70JCE = 32 pin PLCC 70VCE = 32 pin VSOP (8x14mm) JH = 48 ball (BGA 6x8mm) (Call Fac JI = 64 ball (BGA 11x13mm) (Call Fac JS = WLCSP (Call Factory) JW = KGD (Call Factory) E A A A A	Factory)
Blank = First Rev.	020 = 2Mb 040 = 4Mb 080 = 8Mb 016 = 16Mb 032 = 32Mb 064 = 64Mb 128 = 128Mb 256 = 256Mb		Temperature Grade E = Extended grade (-40C to +105C) A1 = Automotive grade (-40C to +85C) A2 = Automotive grade(-40C to +105C) A3 = Automotive grade(-40C to +125C) Blank = Refer to datasheet



ORDERING INFORMATION

Density	Frequency (MHz)	Order Part Number	Package
512K	100	IS39LV512-70JCE	32-pin PLCC
		IS39LV512-70VCE	32-pin VSOP
1M	100	IS39LV010-70JCE	32-pin PLCC
		IS39LV010-70VCE	32-pin VSOP
4M	100	IS39LV040-70JCE	32-pin PLCC
		IS39LV040-70VCE	32-pin VSOP